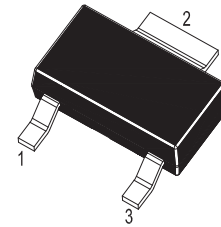
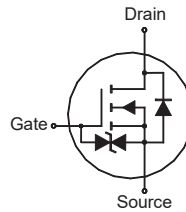


## N-Channel Enhancement Mode MOSFET

### Features

- Built-in G-S Protection Diode
- Halogen and Antimony Free(HAF), RoHS compliant
- ESD Protected
- Typical ESD Protection HBM Class 1C



1.Gate 2.Drain 3.Source  
SOT-223-2 Plastic Package

| Classification | Voltage Range(V) |
|----------------|------------------|
| 0A             | < 125            |
| 0B             | 125 to < 250     |
| 1A             | 250 to < 500     |
| 1B             | 500 to < 1000    |
| 1C             | 1000 to < 2000   |
| 2              | 2000 to < 4000   |
| 3A             | 4000 to < 8000   |
| 3B             | ≥ 8000           |

### Key Parameters

| Parameter        | Value                 | Unit     |
|------------------|-----------------------|----------|
| $BV_{DS}$        | 900                   | V        |
| $R_{DS(ON)}$ Max | 1.4 @ $V_{GS} = 10$ V | $\Omega$ |
| $V_{GS(th)}$ typ | 3                     | V        |
| $Q_g$ typ        | 11 @ $V_{GS} = 10$ V  | nC       |

### Application

- Offline Power Supply

### Absolute Maximum Ratings(at $T_a = 25^\circ\text{C}$ unless otherwise specified)

| Parameter                                        | Symbol         | Value         | Unit             |
|--------------------------------------------------|----------------|---------------|------------------|
| Drain-Source Voltage                             | $V_{DS}$       | 900           | V                |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$      | V                |
| Drain Current                                    | $I_D$          | 2             | A                |
| $T_c = 25^\circ\text{C}$                         |                | 1.4           |                  |
| $T_c = 100^\circ\text{C}$                        |                |               |                  |
| Peak Drain Current, Pulsed <sup>1)</sup>         | $I_{DM}$       | 7             | A                |
| Avalanche Current                                | $I_{AS}$       | 1.5           | A                |
| Single Pulse Avalanche Energy <sup>2)</sup>      | $E_{AS}$       | 97            | mJ               |
| Total Power Dissipation                          | $P_{tot}$      | 12.5          | W                |
| $T_c = 25^\circ\text{C}$                         |                |               |                  |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | - 55 to + 150 | $^\circ\text{C}$ |

### Thermal Characteristics

| Parameter                                                 | Symbol          | Max. | Unit               |
|-----------------------------------------------------------|-----------------|------|--------------------|
| Thermal Resistance from Junction to Case                  | $R_{\theta JC}$ | 10   | $^\circ\text{C/W}$ |
| Thermal Resistance from Junction to Ambient <sup>3)</sup> | $R_{\theta JA}$ | 50   | $^\circ\text{C/W}$ |

<sup>1)</sup> Pulse Test: Pulse Width  $\leq 100 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ , Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ\text{C}$ .

<sup>2)</sup> Limited by  $T_{J(MAX)}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 86 \text{ mH}$ ,  $R_g = 25 \Omega$ ,  $I_D = 1.5 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$ .

<sup>3)</sup> Device Surface Mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate, in a still air.

Characteristics at  $T_a = 25^\circ\text{C}$  unless otherwise specified

| Parameter                                                                                                                  | Symbol       | Min. | Typ. | Max.    | Unit          |
|----------------------------------------------------------------------------------------------------------------------------|--------------|------|------|---------|---------------|
| <b>STATIC PARAMETERS</b>                                                                                                   |              |      |      |         |               |
| Drain-Source Breakdown Voltage<br>at $I_D = 1\text{ mA}$                                                                   | $BV_{DS}$    | 900  | -    | -       | V             |
| Drain-Source Leakage Current<br>at $V_{DS} = 900\text{ V}$                                                                 | $I_{DSS}$    | -    | -    | 1       | $\mu\text{A}$ |
| Gate Leakage Current<br>at $V_{GS} = \pm 20\text{ V}$                                                                      | $I_{GSS}$    | -    | -    | $\pm 1$ | $\mu\text{A}$ |
| Gate-Source Threshold Voltage<br>at $V_{DS} = V_{GS}$ , $I_D = 150\text{ }\mu\text{A}$                                     | $V_{GS(th)}$ | 2    | -    | 4       | V             |
| Drain-Source On-State Resistance<br>at $V_{GS} = 10\text{ V}$ , $I_D = 0.9\text{ A}$                                       | $R_{DS(on)}$ | -    | 1.1  | 1.4     | $\Omega$      |
| <b>DYNAMIC PARAMETERS</b>                                                                                                  |              |      |      |         |               |
| Forward Transconductance<br>at $V_{DS} = 5\text{ V}$ , $I_D = 0.9\text{ A}$                                                | $g_{fs}$     | -    | 2    | -       | S             |
| Gate Resistance<br>at $V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ V}$ , $f = 1\text{ MHz}$                                   | $R_g$        | -    | 4.9  | -       | $\Omega$      |
| Input Capacitance<br>at $V_{GS} = 0\text{ V}$ , $V_{DS} = 450\text{ V}$ , $f = 1\text{ MHz}$                               | $C_{iss}$    | -    | 457  | -       | pF            |
| Output Capacitance<br>at $V_{GS} = 0\text{ V}$ , $V_{DS} = 450\text{ V}$ , $f = 1\text{ MHz}$                              | $C_{oss}$    | -    | 11.4 | -       | pF            |
| Reverse Transfer Capacitance<br>at $V_{GS} = 0\text{ V}$ , $V_{DS} = 450\text{ V}$ , $f = 1\text{ MHz}$                    | $C_{rss}$    | -    | 2    | -       | pF            |
| Gate charge total<br>at $V_{DS} = 450\text{ V}$ , $I_D = 2\text{ A}$ , $V_{GS} = 10\text{ V}$                              | $Q_g$        | -    | 11   | -       | nC            |
| Gate to Source Charge<br>at $V_{DS} = 450\text{ V}$ , $I_D = 2\text{ A}$ , $V_{GS} = 10\text{ V}$                          | $Q_{gs}$     | -    | 3    | -       | nC            |
| Gate to Drain Charge<br>at $V_{DS} = 450\text{ V}$ , $I_D = 2\text{ A}$ , $V_{GS} = 10\text{ V}$                           | $Q_{gd}$     | -    | 3.6  | -       | nC            |
| Turn-On Delay Time<br>at $V_{DS} = 500\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 2\text{ A}$ , $R_g = 24\text{ }\Omega$  | $t_{d(on)}$  | -    | 26   | -       | ns            |
| Turn-On Rise Time<br>at $V_{DS} = 500\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 2\text{ A}$ , $R_g = 24\text{ }\Omega$   | $t_r$        | -    | 21   | -       | ns            |
| Turn-Off Delay Time<br>at $V_{DS} = 500\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 2\text{ A}$ , $R_g = 24\text{ }\Omega$ | $t_{d(off)}$ | -    | 25   | -       | ns            |
| Turn-Off Fall Time<br>at $V_{DS} = 500\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 2\text{ A}$ , $R_g = 24\text{ }\Omega$  | $t_f$        | -    | 98   | -       | ns            |
| <b>Body-Diode PARAMETERS</b>                                                                                               |              |      |      |         |               |
| Drain-Source Diode Forward Voltage<br>at $I_S = 2\text{ A}$ , $V_{GS} = 0\text{ V}$                                        | $V_{SD}$     | -    | -    | 1.3     | V             |
| Body-Diode Continuous Current                                                                                              | $I_S$        | -    | -    | 2       | A             |
| Body-Diode Continuous Current, Pulsed                                                                                      | $I_{SM}$     | -    | -    | 7       | A             |
| Body Diode Reverse Recovery Time<br>at $I_S = 2\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$                             | $t_{rr}$     | -    | 222  | -       | ns            |
| Body Diode Reverse Recovery Charge<br>at $I_S = 2\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$                           | $Q_{rr}$     | -    | 1.6  | -       | $\mu\text{C}$ |

## Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

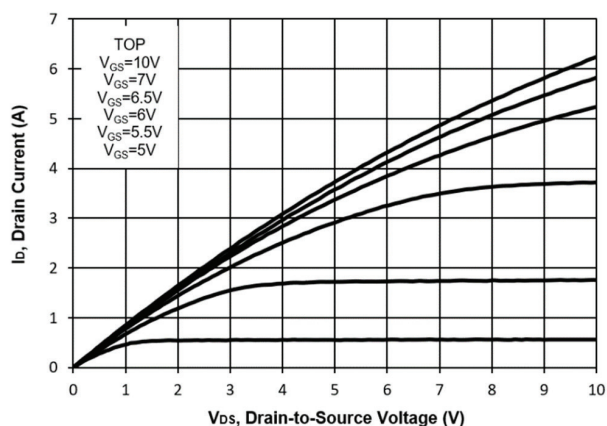


Fig. 2 Typical Transfer Characteristics

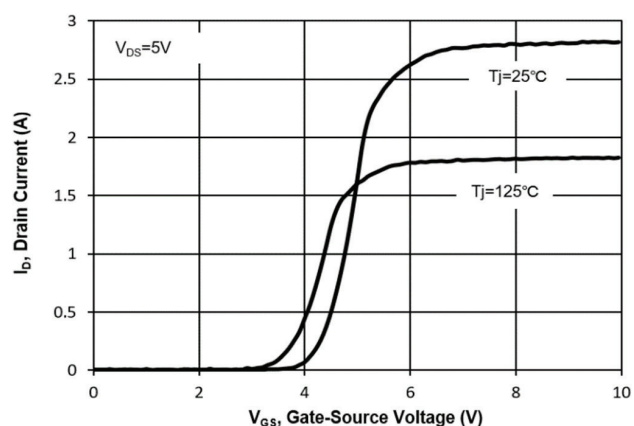


Fig. 3 On-Resistance vs. Drain Current

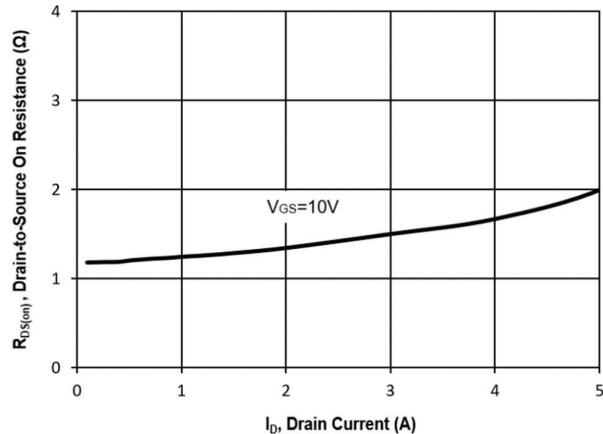


Fig. 4 On-Resistance vs. Gate-Source Voltage

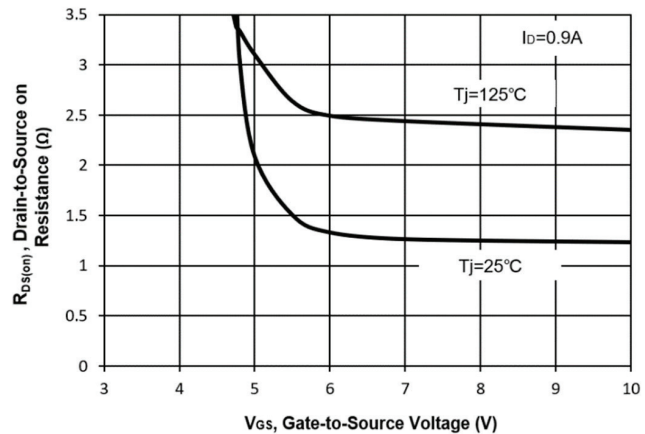


Fig. 5 On-Resistance vs. Tj

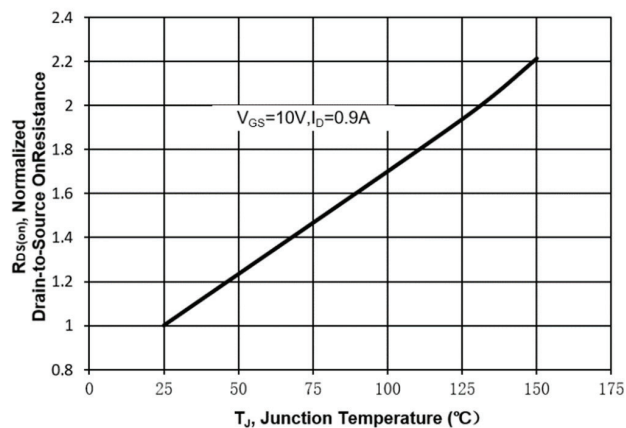
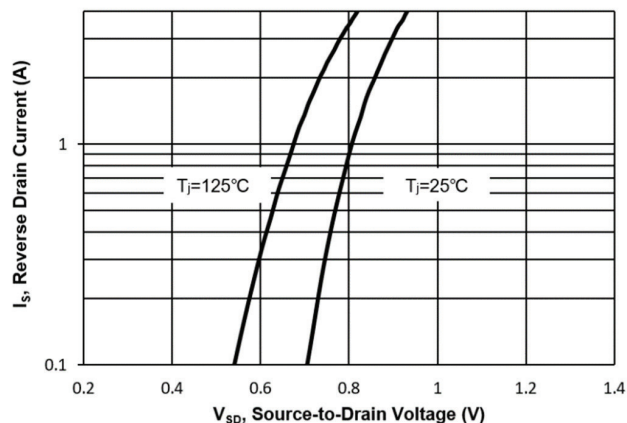


Fig. 6 Typical Forward Characteristics



## Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

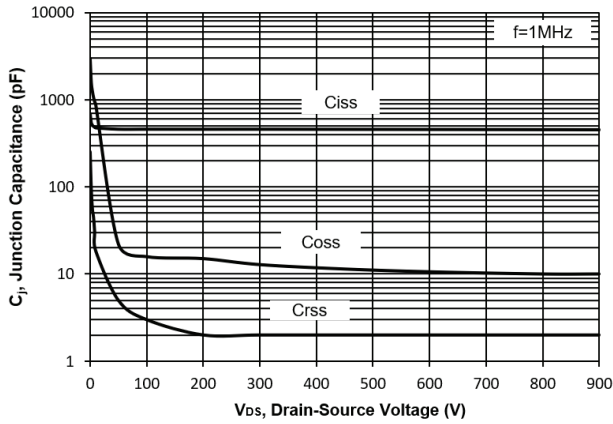


Fig. 8 Drain-Source Leakage Current vs. T<sub>J</sub>

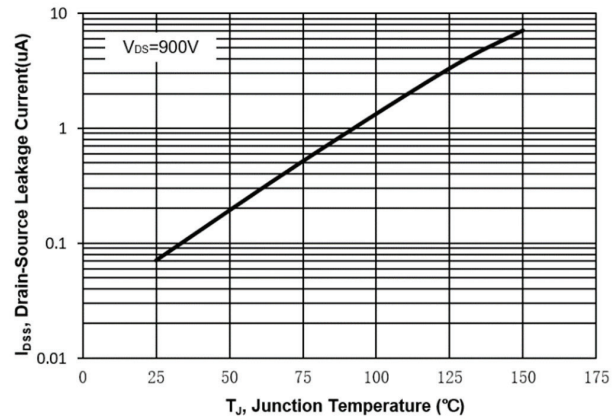


Fig. 9 V<sub>(BR)DSS</sub> vs. Junction Temperature

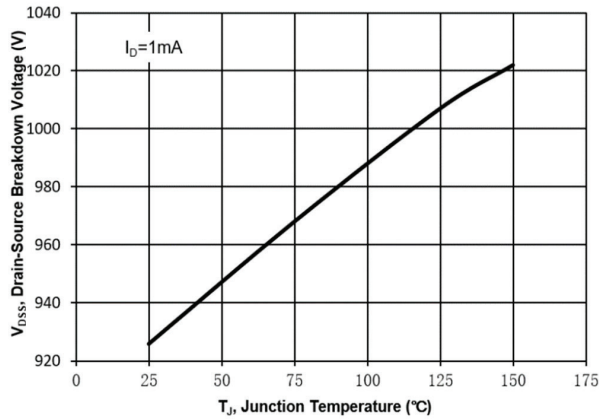


Fig. 10 Gate Threshold Variation vs. T<sub>J</sub>

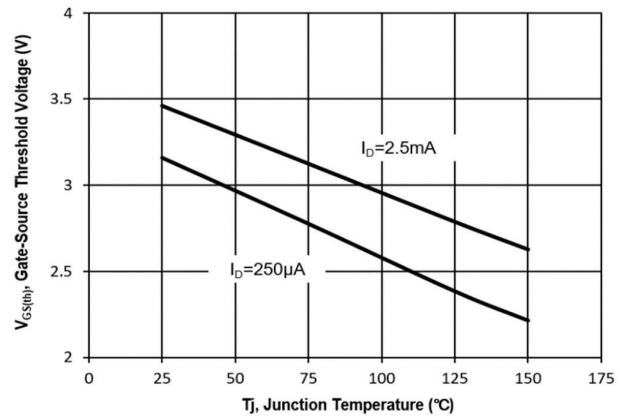


Fig. 11 Gate Charge

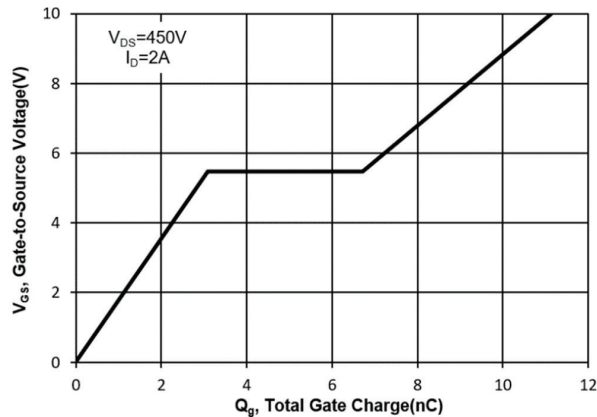


Fig. 12 Safe Operation Area

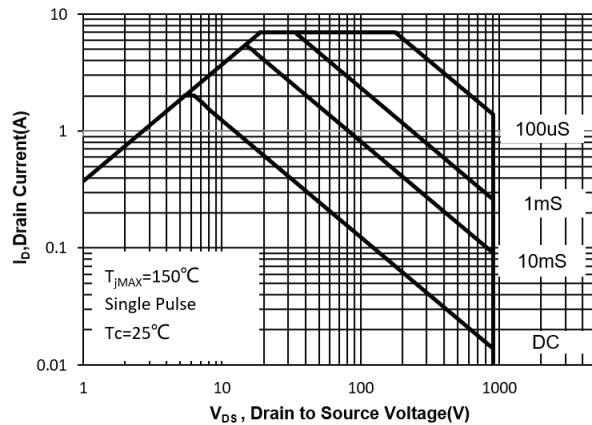


Fig.13 Normalized maximum transient thermal impedance( $z_{\theta JC}$ )

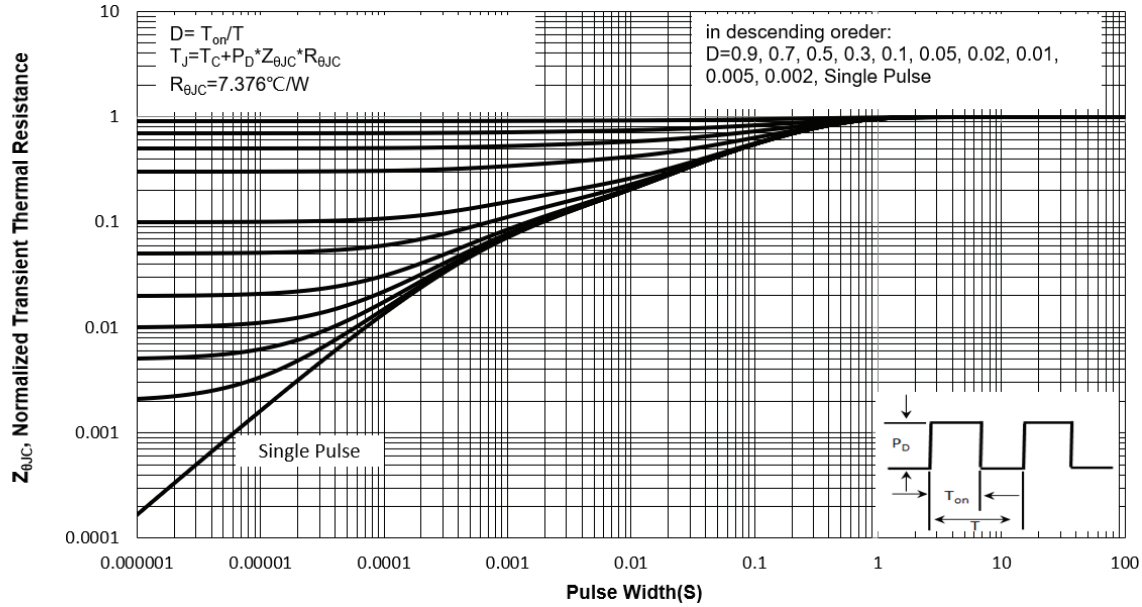
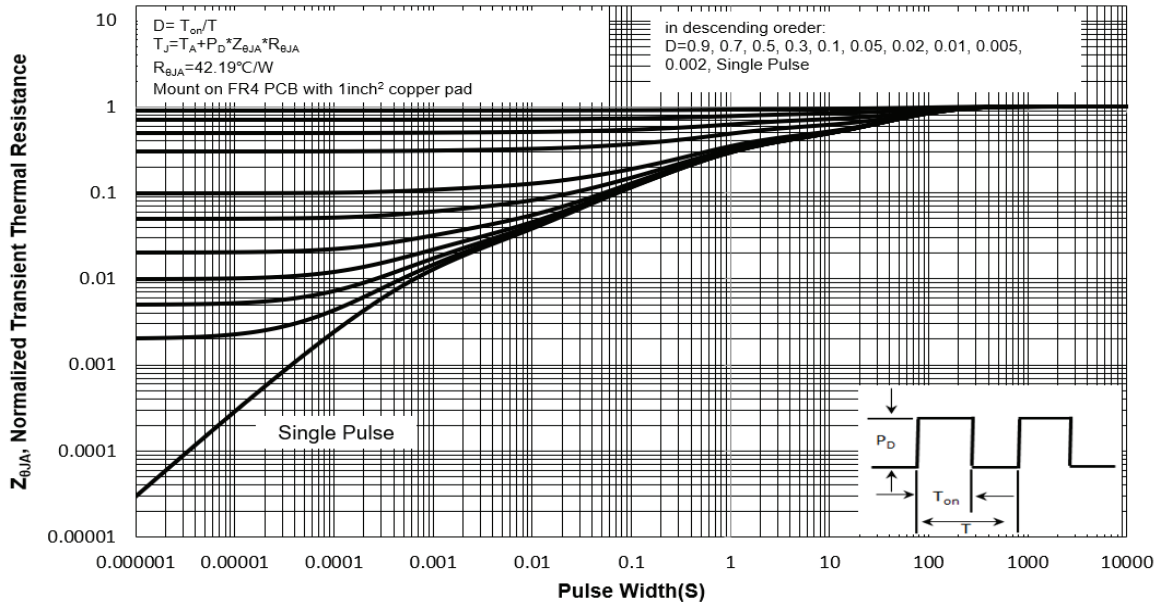


Fig.14 Normalized Maximum Transient Thermal Impedance( $z_{\theta JA}$ )



## Test Circuits

Fig.1-1 Switching times test circuit

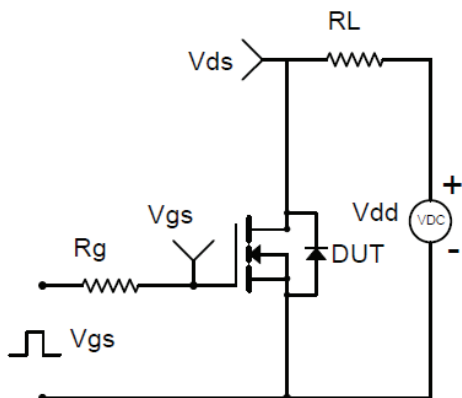


Fig.1-2 Switching Waveform

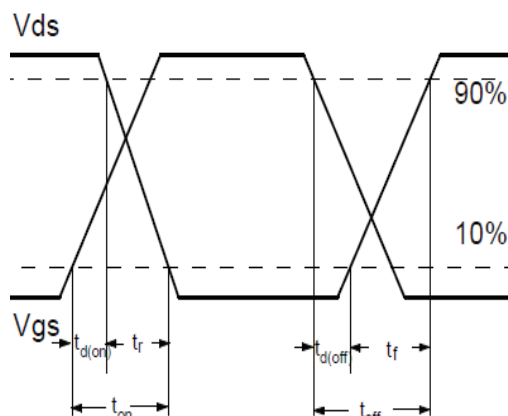


Fig.2-1 Gate charge test circuit

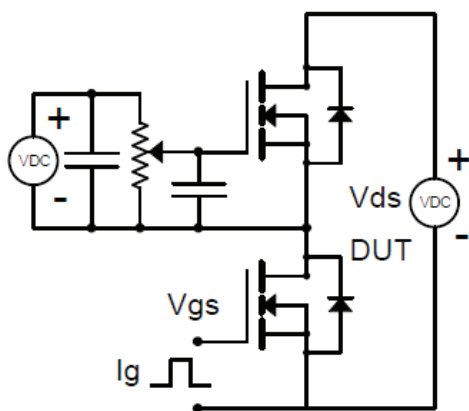


Fig.2-2 Gate charge waveform

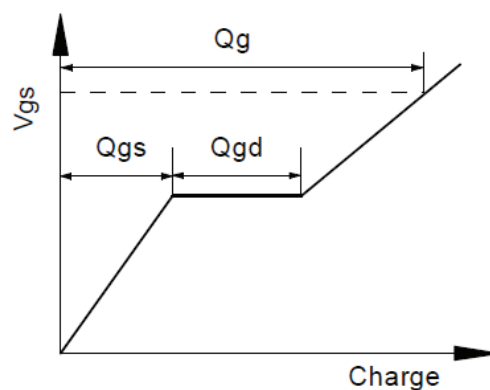


Fig.3-1 Avalanche test circuit

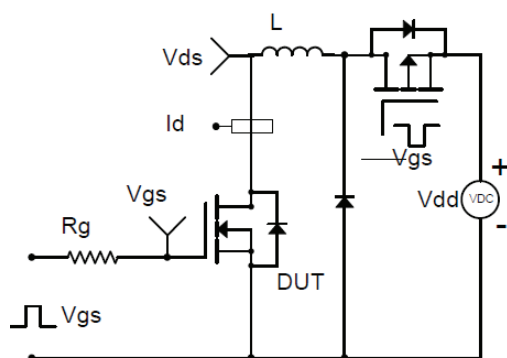
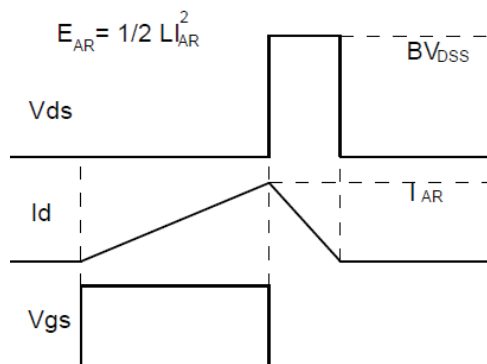
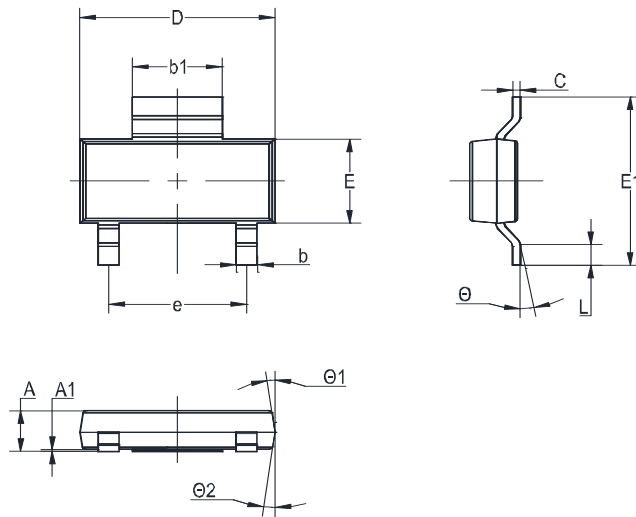
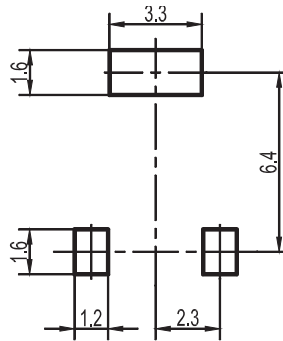


Fig.3-2 Avalanche waveform



**PACKAGE OUTLINE (Dimensions in mm)**
**SOT-223-2**


| Unit | A          | A1         | b          | b1         | C            | D          | E          | E1         | e          | L          | Θ         | Θ1       | Θ2       |
|------|------------|------------|------------|------------|--------------|------------|------------|------------|------------|------------|-----------|----------|----------|
| mm   | 1.8<br>1.5 | 0.1<br>MAX | 0.8<br>0.6 | 3.1<br>2.9 | 0.32<br>0.22 | 6.7<br>6.3 | 3.7<br>3.3 | 7.3<br>6.7 | 4.6<br>TYP | 1.1<br>0.7 | 10°<br>0° | 7°<br>0° | 7°<br>0° |

**Recommended Soldering Footprint**

**Packing information**

| Package   | Tape Width (mm) | Pitch   |               | Reel Size |      | Per Reel Packing Quantity |
|-----------|-----------------|---------|---------------|-----------|------|---------------------------|
|           |                 | mm      | inch          | mm        | inch |                           |
| SOT-223-2 | 12              | 8 ± 0.1 | 0.315 ± 0.004 | 330       | 13   | 3,000                     |

**Marking information**

" PDQ90N1K5K " = Part No

" \*\*\*\*\* " = Date Code Marking

Font type: Arial



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